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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/644,417	08/20/2003	Jack Hwang	ITL.0764D1US (P14416D)	ITL.0764D1US (P14416D) 6957	
75	90 08/26/2004		EXAMINER		
TROP, PRUNER & HU, P.C.			PRENTY,	PRENTY, MARK V	
Suite 100 8554 Katy Freeway			ART UNIT	PAPER NUMBER	
Houston, TX 77024			2822		
			DATE MAILED: 08/26/200-	DATE MAILED: 08/26/2004	

Please find below and/or attached an Office communication concerning this application or proceeding.

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		Application No.	Applicant(s)
Office Action Summary		10/644,417	HWANG ET AL.
		Examiner	Art Unit
		MARK V PRENTY	2822
Period f	The MAILING DATE of this communication apports or Reply	pears on the cover sheet wi	h the correspondence address
THE - Exte after - If th - If NO - Failt Any	MORTENED STATUTORY PERIOD FOR REPL MAILING DATE OF THIS COMMUNICATION. ensions of time may be available under the provisions of 37 CFR 1.1 r SIX (6) MONTHS from the mailing date of this communication. e period for reply specified above is less than thirty (30) days, a repl of period for reply is specified above, the maximum statutory period for reply within the set or extended period for reply will, by statute reply received by the Office later than three months after the mailing the patent term adjustment. See 37 CFR 1.704(b).	136(a). In no event, however, may a re ly within the statutory minimum of thirt will apply and will expire SIX (6) MON' e, cause the application to become AB	oply be timely filed  r (30) days will be considered timely.  FHS from the mailing date of this communication.  ANDONED (35 U.S.C. § 133).
Status			
1)⊠ 2a)⊠ 3)□	· · · <u> </u>	s action is non-final. Ince except for formal matte	. •
Dienneit	ion of Claims	ex parto quayro, 1000 0.2	11, 100 0.0. 210.
5)□ 6)⊠	Claim(s) 20-24 is/are pending in the applicatio 4a) Of the above claim(s) is/are withdra Claim(s) is/are allowed. Claim(s) 20-24 is/are rejected. Claim(s) is/are objected to. Claim(s) are subject to restriction and/or	wn from consideration.	
Applicat	ion Papers		
10)	The specification is objected to by the Examine The drawing(s) filed on is/are: a) acc Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct The oath or declaration is objected to by the Ex	cepted or b) objected to to determine or b) objected to to drawing(s) be held in abeyand tion is required if the drawing(	ce. See 37 CFR 1.85(a). s) is objected to. See 37 CFR 1.121(d).
Priority (	under 35 U.S.C. § 119		
a)	Acknowledgment is made of a claim for foreign All b) Some * c) None of:  1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the priority application from the International Bureau See the attached detailed Office action for a list	ts have been received. ts have been received in Aprity documents have been u (PCT Rule 17.2(a)).	oplication No received in this National Stage
Attachmen	nt(s)	_	
2) 🔲 Notic 3) 🔲 Infori	ce of References Cited (PTO-892) ce of Draftsperson's Patent Drawing Review (PTO-948) mation Disclosure Statement(s) (PTO-1449 or PTO/SB/08) or No(s)/Mail Date	Paper No(s	ummary (PTO-413) //Mail Date formal Patent Application (PTO-152) 

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This Office Action is in response to the amendment filed on August 13, 2004.

That amendment has been entered.

The specification's reference (on page 1) to the parent application should be amended/updated to include its patented status.

Claims 20-24 are rejected under 35 U.S.C. 102(e) as being anticipated by Yu (United States Patent 6,368,947 – hereafter Yu '947 – already of record).

With respect to independent claim 20, Yu '947 discloses an integrated circuit (see the entire patent, including the Fig. 2 disclosure) comprising: a semiconductor structure 14; a gate 36 formed on said semiconductor structure; and a P-type source 40 and a P-type drain region 40, said source and drain region including both germanium (see column 5, lines 38-62) and a P-type source/drain impurity (i.e., boron - see col. 5, lines 63-67), said source and drain regions being strained (by virtue of the germanium implant being higher than the boron implant – see column 5, lines 55-57 and 63-67).

Claim 20 is thus rejected under 35 U.S.C. 102(e) as being anticipated by Yu '947.

With respect to dependent claim 21, Yu '947's ratio of germanium to P-type source/drain impurity is greater than one to one (see column 5, lines 55-57 and 63-67).

Claim 21 is thus rejected under 35 U.S.C. 102(e) as being anticipated by Yu '947.

With respect to dependent claim 22, Yu '947's ratio of germanium to P-type source/drain impurity is approximately four to one (see col. 5, lines 55-57 and 63-67).

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Claim 22 is thus rejected under 35 U.S.C. 102(e) as being anticipated by Yu '947.

With respect to dependent claim 23, Yu '947's source and drain regions 40 are source and drain extensions (see Fig. 3 together with column 4, lines 22-30).

Claim 23 is thus rejected under 35 U.S.C. 102(e) as being anticipated by Yu '947.

With respect to dependent claim 24, Yu '947's implanted region 40 is a source/drain extension (see Fig. 3 together with column 4, lines 22-30).

Claim 24 is thus rejected under 35 U.S.C. 102(e) as being anticipated by Yu '947.

Claims 20, 23 and 24 are rejected under 35 U.S.C. 102(e) as being anticipated by Liu et al. (United States Patent Application Publication US 2002/0086502 – hereafter Liu – already of record).

With respect to independent claim 20, Liu discloses an integrated circuit (see the entire patent, including the Fig. 6 disclosure) comprising: a semiconductor structure 102; a gate 106 formed on said semiconductor structure; and a P-type source 122 and a P-type drain region 122, said source and drain region including both germanium (see paragraph [0016]) and a P-type source/drain impurity (see paragraph [0017]), said source and drain regions being strained (by virtue of the germanium and P-type impurity implants being different – see paragraphs [0016] and [0017]).

Claim 20 is thus rejected under 35 U.S.C. 102(e) as being anticipated by Liu.

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With respect to dependent claim 23, Liu's source and drain regions 122 are source and drain extensions (see paragraph [0018]).

Claim 23 is thus rejected under 35 U.S.C. 102(e) as being anticipated by Liu.

With respect to dependent claim 24, Liu's implanted region 122 is a source/drain extension (see paragraph [0018]).

Claim 24 is thus rejected under 35 U.S.C. 102(e) as being anticipated by Liu.

The applicant's argument with respect to the rejection of claims 20-24 under 35 U.S.C. 102(e) as being anticipated by Yu '947 is not persuasive because the applicant fails to even address, let alone rebut, the rationale provided in the last Office Action. Specifically, the applicant fails to even address, let alone rebut, the last Office Action's explanation (on page 7) that: "the ratio of germanium to P-type impurities in Yu '947's region 40 (Fig. 2) is greater than one (thus resulting in a strained junction) because region 40's germanium concentration is higher than its P-type impurities concentration (by virtue of the germanium being implanted at a higher dose than the P-type impurities and to the same depth)."

Given that the applicant does not dispute that the ratio of germanium to P-type impurities in Yu '947's source/drain region 40 is greater than one and given that the applicant's specification discloses that such results in a strained junction (see paragraph [0023]), the applicant's argument with respect to the rejection of claims 20-24 under 35 U.S.C. 102(e) as being anticipated by Yu '947 is not persuasive.

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The applicant's argument with respect to the rejection of claims 20, 23 and 24 under 35 U.S.C. 102(e) as being anticipated by Liu is not persuasive because the applicant fails to even address, let alone rebut, the rationale provided in the last Office Action. Specifically, the applicant fails to even address, let alone rebut, the last Office Action's explanation (in the paragraph bridging pages 7-8) that: "Liu's source/drain region 122 (Fig. 6) is strained because its germanium concentration is different than its P-type impurities concentration (by virtue of the germanium being implanted at a different dose than the P-type impurities and to the same depth)."

Given that the applicant does not dispute that the germanium concentration and the P-type impurities concentration in Liu's source/drain region 122 are different and given that the applicant's specification discloses that such results in a strained junction (see paragraph [0023]), the applicant's argument with respect to the rejection of claims 20, 23 and 24 under 35 U.S.C. 102(e) as being anticipated by Liu is not persuasive.

Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the

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shortened statutory period will expire on the date the advisory action is mailed, and any

extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of

the advisory action. In no event, however, will the statutory period for reply expire later

than SIX MONTHS from the date of this final action.

Registered practitioners can telephone the examiner at (571) 272-1843. Any

voicemail message left for the examiner must include the name and registration number

of the registered practitioner calling, and the Application/Control (Serial) Number.

Technology Center 2800's general telephone number is (571) 272-2800.

Mark V. Prenty Primary Examiner

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